

# STTH1008DTI

## 800 V tandem hyperfast diode

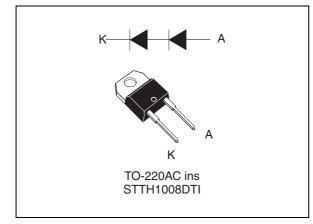
#### Datasheet – production data



- High voltage rectifier
- Tandem diodes in series
- Very low switching losses
- Insulated device with internal ceramic
- Equal thermal conditions for both 400 V diodes
- Static and dynamic equilibrium of internal diodes are warranted by design

### Description

The STTH1008DTI is an ultrahigh performance diode composed of two 400 V dice in series.



### Table 1. Device summary

I <sub>F(AV)</sub>	10 A
I <sub>FRM</sub>	20 A
V <sub>RRM</sub>	800 V
t <sub>rr</sub>	40 ns
I <sub>RM</sub>	8.5 A
V <sub>F</sub>	1.7 V
Tj	150 °C

This is information on a product in full production.

# 1 Characteristics

### Table 2. Absolute ratings (limiting values per diode at 25 °C, unless otherwise specified)

Symbol	Parameter	Value	Unit	
V <sub>RRM</sub>	Repetitive peak reverse voltage	800	V	
I <sub>F(RMS)</sub>	Forward rms current	16	А	
I <sub>F(AV)</sub>	Average forward current, $\delta = 0.5$ $T_c = 85 \text{ °C}$		10	А
I <sub>FRM</sub>	Repetitive peak forward current $T_c = 135 \text{ °C}, \delta = 0.3$		20	А
I <sub>FSM</sub>	Surge non repetitive forward current	120	А	
T <sub>stg</sub>	Storage temperature range	-65 to +175	°C	
Тj	Maximum junction temperature		150	°C

### Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub>	Junction to case	2.5	°C/W

### Table 4. Static electrical characteristics

Symbol	Parameters	Test conditions		Min.	Тур	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Povorco logkago current	T <sub>j</sub> = 25 °C	V - V			20	
IR <sup>(1)</sup> Reverse leakage current	T <sub>j</sub> = 150 °C	$V_{R} = V_{RRM}$		20	200	μA	
	V <sub>F</sub> <sup>(2)</sup> Forward voltage drop	T <sub>c</sub> = 25 °C	I <sub>F</sub> = 10 A		2.15	2.5	
V (2)		T <sub>c</sub> = 150 °C	IF - 10 A		1.7	2.05	V
۷F		T <sub>c</sub> = 25 °C	I <sub>F</sub> = 20 A		2.45	2.85	v
		T <sub>c</sub> = 150 °C	IF = 20 A		2.05	2.45	

1. Pulse test:  $t_{\scriptscriptstyle P}$  = 5 ms,  $\delta$  < 2%

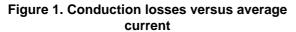
2. Pulse test:  $t_P = 380 \ \mu s, \ \delta < 2\%$ 

To evaluate the conduction losses use the following equation:

 $P = 1.65 \text{ x } I_{F(AV)} + 0.04 \text{ x } {I_{F}}^{2}_{(RMS)}$ 



Symbol	Parameters	Test conditions		Min.	Тур	Max.	Unit
I <sub>RM</sub>	Reverse recovery current	T <sub>i</sub> = 125 °C	$T_j = 125 \text{ °C}$ $I_F = 10 \text{ A}, V_R = 400 \text{ V},  dI_F/dt = -200 \text{ A}/\mu \text{s}$		8.5	11.5	А
S <sub>factor</sub>	Softness factor	,			0.8		
+	Reverse recovery time	$T_j = 25 \text{ °C}$ $I_F = 1 \text{ A}, V_R = 30 \text{ V}, \\ dI_F/dt = -50 \text{ A}/\mu \text{s}$		40	55	ns	
t <sub>rr</sub>		T <sub>j</sub> = 125 °C	$T_{j} = 125 \text{ °C} \qquad \begin{matrix} I_{F} = 10 \text{ A},  V_{R} = 400 \text{ V}, \\ dI_{F}/dt = -200 \text{ A}/\mu\text{s} \end{matrix}$		80		
t <sub>fr</sub>	Forward recovery time	T <sub>j</sub> = 25 °C				180	ns
$V_{FP}$	Forward recovery voltage	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 10 A, V <sub>FR</sub> = 3 V, dI <sub>F</sub> /dt = 100 A/μs		4.5	7	V



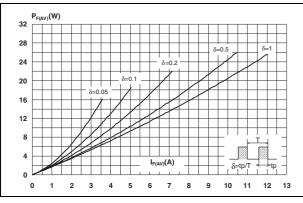
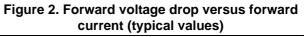
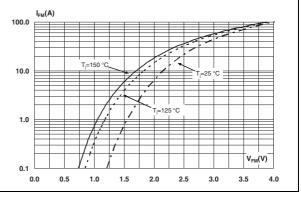
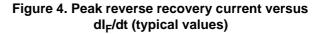
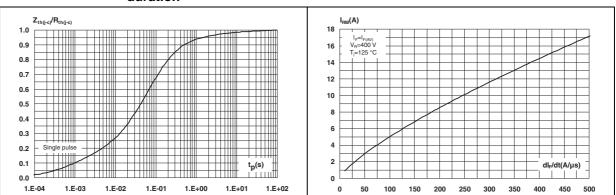


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration









#### Figure 5. Reverse recovery time versus dl<sub>F</sub>/dt (typical values)

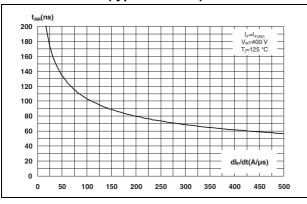


Figure 7. Reverse recovery softness factor versus dl<sub>F</sub>/dt (typical values)

#### Figure 6. Reverse recovery charges versus dl<sub>F</sub>/dt (typical values)

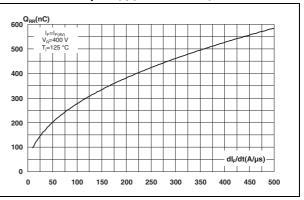


Figure 8. Relative variations of dynamic parameters versus junction temperature

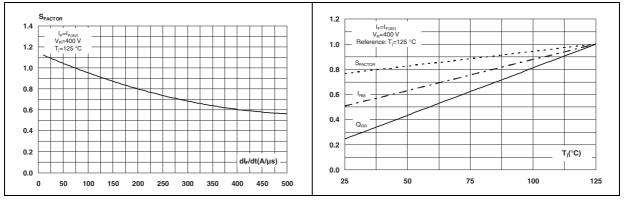
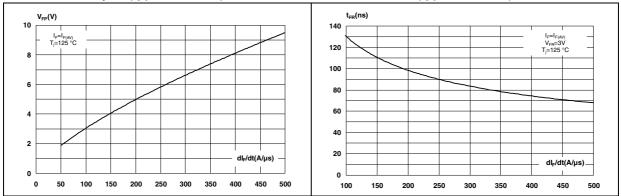


Figure 9. Transient peak forward voltage versus Figure 10. Forward recovery time versus dl<sub>F</sub>/dt dl<sub>F</sub>/dt (typical values)

(typical values)





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100	C(pF)	F=1 N	nHz -
		V <sub>osc</sub> =30 T <sub>j</sub> =25	mV <sub>RMS</sub>
10			
1			V <sub>R</sub> (V)
	1 10	100	1000

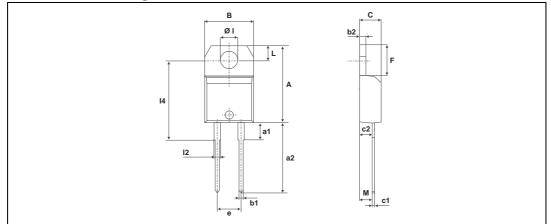
Figure 11. Junction capacitance versus reverse voltage applied (typical values)



# 2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque: 0.4 to 0.6 N·m

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#### Figure 12. TO-220AC ins dimension definitions



	Dimensions							
Ref.		Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.		
А	15.20		15.90	0.598		0.625		
a1		3.75			0.147			
a2	13.00		14.00	0.511		0.551		
В	10.00		10.40	0.393		0.409		
b1	0.61		0.88	0.024		0.034		
b2	1.23		1.32	0.048		0.051		
С	4.40		4.60	0.173		0.181		
c1	0.49		0.70	0.019		0.027		
c2	2.40		2.72	0.094		0.107		
е	4.80		5.40	0.189		0.212		
F	6.20		6.60	0.244		0.259		
ØI	3.75		3.85	0.147		0.151		
14	15.80	16.40	16.80	0.622	0.646	0.661		
L	2.65		2.95	0.104		0.116		
12	1.14		1.70	0.044		0.066		
М		2.60			0.102			

Table 6. TO-220AC ins dimension values



# **3** Ordering information

Table	7.	Ordering	information
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Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH1008DTI	STTH1008DTI	TO-220AC insulated	2.3 g	50	Tube

# 4 Revision history

### Table 8. Document revision history

Date	Revision	Changes
05-Mar-2013	1	Initial release.



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